Lattice Semiconductor Corporation - LFXP2-30E-6F672C Datasheet



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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	3625
Number of Logic Elements/Cells	29000
Total RAM Bits	396288
Number of I/O	472
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-30e-6f672c

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LatticeXP2 Family Data Sheet Introduction

February 2012

Features

- flexiFLASH[™] Architecture
 - Instant-on
 - Infinitely reconfigurable
 - Single chip
 - FlashBAK[™] technology
 - Serial TAG memory
 - Design security

Live Update Technology

- TransFR[™] technology
- Secure updates with 128 bit AES encryption
- Dual-boot with external SPI

■ sysDSP[™] Block

- Three to eight blocks for high performance Multiply and Accumulate
- 12 to 32 18x18 multipliers
- Each block supports one 36x36 multiplier or four 18x18 or eight 9x9 multipliers

Embedded and Distributed Memory

- Up to 885 Kbits sysMEM[™] EBR
- Up to 83 Kbits Distributed RAM

■ sysCLOCK[™] PLLs

- Up to four analog PLLs per device
- Clock multiply, divide and phase shifting

Flexible I/O Buffer

- sysIO[™] buffer supports:
 - LVCMOS 33/25/18/15/12; LVTTL
 - SSTL 33/25/18 class I, II
 - HSTL15 class I; HSTL18 class I, II
 - PCI
 - LVDS, Bus-LVDS, MLVDS, LVPECL, RSDS
- Pre-engineered Source Synchronous Interfaces
 - DDR / DDR2 interfaces up to 200 MHz
 - 7:1 LVDS interfaces support display applications
 - XGMII
- Density And Package Options
 - 5k to 40k LUT4s, 86 to 540 I/Os
 - csBGA, TQFP, PQFP, ftBGA and fpBGA packages
 - Density migration supported
- Flexible Device Configuration
 - SPI (master and slave) Boot Flash Interface
 - Dual Boot Image supported
 - Soft Error Detect (SED) macro embedded

System Level Support

- IEEE 1149.1 and IEEE 1532 Compliant
- · On-chip oscillator for initialization & general use
- Devices operate with 1.2V power supply

Device	XP2-5	XP2-8	XP2-17	XP2-30	XP2-40
LUTs (K)	5	8	17	29	40
Distributed RAM (KBits)	10	18	35	56	83
EBR SRAM (KBits)	166	221	276	387	885
EBR SRAM Blocks	9	12	15	21	48
sysDSP Blocks	3	4	5	7	8
18 x 18 Multipliers	12	16	20	28	32
V _{CC} Voltage	1.2	1.2	1.2	1.2	1.2
GPLL	2	2	4	4	4
Max Available I/O	172	201	358	472	540
Packages and I/O Combinations					•
132-Ball csBGA (8 x 8 mm)	86	86			
144-Pin TQFP (20 x 20 mm)	100	100			
208-Pin PQFP (28 x 28 mm)	146	146	146		
256-Ball ftBGA (17 x17 mm)	172	201	201	201	
484-Ball fpBGA (23 x 23 mm)			358	363	363
672-Ball fpBGA (27 x 27 mm)				472	540

Table 1-1. LatticeXP2 Family Selection Guide

Data Sheet DS1009

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LatticeXP2 Family Data Sheet Architecture

August 2014

Data Sheet DS1009

Architecture Overview

Each LatticeXP2 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM[™] Embedded Block RAM (EBR) and a row of sys-DSP[™] Digital Signal Processing blocks as shown in Figure 2-1.

On the left and right sides of the Programmable Functional Unit (PFU) array, there are Non-volatile Memory Blocks. In configuration mode the nonvolatile memory is programmed via the IEEE 1149.1 TAP port or the sysCONFIG[™] peripheral port. On power up, the configuration data is transferred from the Non-volatile Memory Blocks to the configuration SRAM. With this technology, expensive external configuration memory is not required, and designs are secured from unauthorized read-back. This transfer of data from non-volatile memory to configuration SRAM via wide busses happens in microseconds, providing an "instant-on" capability that allows easy interfacing in many applications. LatticeXP2 devices can also transfer data from the sysMEM EBR blocks to the Non-volatile Memory Blocks at user request.

There are two kinds of logic blocks, the PFU and the PFU without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

LatticeXP2 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large dedicated 18Kbit memory blocks. Each sysMEM block can be configured in a variety of depths and widths of RAM or ROM. In addition, LatticeXP2 devices contain up to two rows of DSP Blocks. Each DSP block has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysIO buffers. The sysIO buffers of the LatticeXP2 devices are arranged into eight banks, allowing the implementation of a wide variety of I/O standards. PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as 7:1 LVDS interfaces, found in many display applications, and memory interfaces including DDR and DDR2.

The LatticeXP2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

Other blocks provided include PLLs and configuration functions. The LatticeXP2 architecture provides up to four General Purpose PLLs (GPLL) per device. The GPLL blocks are located in the corners of the device.

The configuration block that supports features such as configuration bit-stream de-encryption, transparent updates and dual boot support is located between banks two and three. Every device in the LatticeXP2 family supports a sysCONFIG port, muxed with bank seven I/Os, which supports serial device configuration. A JTAG port is provided between banks two and three.

This family also provides an on-chip oscillator. LatticeXP2 devices use 1.2V as their core voltage.

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Figure 2-3. Slice Diagram



DI[3:2] for Slice 2 and DI[1:0] for Slice 0 data

WAD [A:D] is a 4bit address from slice 1 LUT input

Table 2-2. Slice Signal Descriptions

Function	Туре	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	MO	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCI	Fast Carry-In ¹
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6 and LUT7
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6 and LUT7
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 ² MUX depending on the slice
Output	Inter-PFU signal	FCO	Slice 2 of each PFU is the fast carry chain output ¹

1. See Figure 2-3 for connection details.

2. Requires two PFUs.



Figure 2-6. Primary Clock Sources for XP2-17



Note: This diagram shows sources for the XP2-17 device. Smaller LatticeXP2 devices have two GPLLs.



Figure 2-16. FlashBAK Technology



Memory Cascading

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports two forms of write behavior for single port or dual port operation:

- 1. Normal Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. GSRN, the global reset signal, resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-17.

Figure 2-17. Memory Core Reset





IPexpress[™]

The user can access the sysDSP block via the Lattice IPexpress tool, which provides the option to configure each DSP module (or group of modules), or by direct HDL instantiation. In addition, Lattice has partnered with The Math-Works[®] to support instantiation in the Simulink[®] tool, a graphical simulation environment. Simulink works with Diamond to dramatically shorten the DSP design cycle in Lattice FPGAs.

Optimized DSP Functions

Lattice provides a library of optimized DSP IP functions. Some of the IP cores planned for the LatticeXP2 DSP include the Bit Correlator, FFT functions, FIR Filter, Reed-Solomon Encoder/Decoder, Turbo Encoder/Decoder and Convolutional Encoder/Decoder. Please contact Lattice to obtain the latest list of available DSP IP cores.

Resources Available in the LatticeXP2 Family

Table 2-8 shows the maximum number of multipliers for each member of the LatticeXP2 family. Table 2-9 shows the maximum available EBR RAM Blocks and Serial TAG Memory bits in each LatticeXP2 device. EBR blocks, together with Distributed RAM can be used to store variables locally for fast DSP operations.

Device	DSP Block	9x9 Multiplier	18x18 Multiplier	36x36 Multiplier
XP2-5	3	24	12	3
XP2-8	4	32	16	4
XP2-17	5	40	20	5
XP2-30	7	56	28	7
XP2-40	8	64	32	8

Table 2-8. Maximum Number of DSP Blocks in the LatticeXP2 Family

Table 2-9. Embedded SRAM/TAG Memor	v in the LatticeXP2 Family

Device	EBR SRAM Block	Total EBR SRAM (Kbits)	TAG Memory (Bits)
XP2-5	9	166	632
XP2-8	12	221	768
XP2-17	15	276	2184
XP2-30	21	387	2640
XP2-40	48	885	3384

LatticeXP2 DSP Performance

Table 2-10 lists the maximum performance in Millions of MAC (MMAC) operations per second for each member of the LatticeXP2 family.

Table 2-10. DSP Performance

Device	DSP Block	DSP Performance MMAC
XP2-5	3	3,900
XP2-8	4	5,200
XP2-17	5	6,500
XP2-30	7	9,100
XP2-40	8	10,400

For further information on the sysDSP block, please see TN1140, <u>LatticeXP2 sysDSP Usage Guide</u>.



The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred from the DQS to system clock domain. For further discussion on this topic, see the DDR Memory section of this data sheet.





Output Register Block

The output register block provides the ability to register signals from the core of the device before they are passed to the sysIO buffers. The blocks on the PIOs on the left, right and bottom contain registers for SDR operation that are combined with an additional latch for DDR operation. Figure 2-27 shows the diagram of the Output Register Block for PIOs.

In SDR mode, ONEG0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, ONEG0 and OPOS0 are fed into registers on the positive edge of the clock. At the next clock cycle the registered OPOS0 is latched. A multiplexer running off the same clock cycle selects the correct register to feed the output (D0).

By combining output blocks of the complementary PIOs and sharing some registers from input blocks, a gearbox function can be implemented, to take four data streams ONEG0A, ONEG1A, ONEG1B and ONEG1B. Figure 2-27



DQSXFER

LatticeXP2 devices provide a DQSXFER signal to the output buffer to assist it in data transfer to DDR memories that require DQS strobe be shifted 90°. This shifted DQS strobe is generated by the DQSDEL block. The DQSXFER signal runs the span of the data bus.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement the wide variety of standards that are found in today's systems including LVCMOS, SSTL, HSTL, LVDS and LVPECL.

sysIO Buffer Banks

LatticeXP2 devices have eight sysIO buffer banks for user I/Os arranged two per side. Each bank is capable of supporting multiple I/O standards. Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank has voltage references, V_{REF1} and V_{REF2} , that allow it to be completely independent from the others. Figure 2-32 shows the eight banks and their associated supplies.

In LatticeXP2 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO} . LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO} .

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2} , that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

тор

Figure 2-32. LatticeXP2 Banks



воттом



original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, <u>LatticeXP2 Dual Boot Feature</u>.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

- 1. Device powers up with the default CCLK frequency.
- 2. During configuration, users select a different CCLK frequency.
- 3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, <u>LatticeXP2 sysCON-FIG Usage Guide</u>.

Table 2-14. Selectable	CCLKs and Oscillato	r Freauencies Durina	Configuration and	User Mode

CCLK/Oscillator (MHz)
2.5 ¹
3.1 ²
4.3
5.4
6.9
8.1
9.2
10
13
15
20
26
32
40
54
80 ³
163 ³
1 Software default oscillator frequency

1. Software default oscillator frequency.

2. Software default CCLK frequency.

3. Frequency not valid for CCLK.



Density Shifting

The LatticeXP2 family is designed to ensure that different density devices in the same family and in the same package have the same pinout. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case.



Hot Socketing Specifications^{1, 2, 3, 4}

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{DK}	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX.)	_	_	+/-1	mA

1. Insensitive to sequence of V_{CC} , V_{CCAUX} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} , V_{CCAUX} and V_{CCIO} .

2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX) or $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).

3. I_{DK} is additive to I_{PU} , I_{PW} or I_{BH} .

4. LVCMOS and LVTTL only.

ESD Performance

Please refer to the <u>LatticeXP2 Product Family Qualification Summary</u> for complete qualification data, including ESD performance.

DC Electrical Characteristics

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I., I., ¹	Input or I/O Low Lookago	$0 \le V_{IN} \le V_{CCIO}$	—		10	μΑ
'IL', 'IH	input of i/O Low Leakage	$V_{CCIO} \le V_{IN} \le V_{IH}$ (MAX)	—	—	150	μΑ
I _{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7 \ V_{CCIO}$	-30	—	-150	μΑ
I _{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\leq V_{IN} \leq V_{CCIO}$	30		210	μΑ
I _{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	μΑ
I _{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μΑ
I _{BHLO}	Bus Hold Low Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—		210	μΑ
I _{BHHO}	Bus Hold High Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	-150	μΑ
V _{BHT}	Bus Hold Trip Points		V_{IL} (MAX)	_	V _{IH} (MIN)	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	8	—	pf
C2	Dedicated Input Capacitance	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	6	—	pf

Over Recommended Operating Conditions

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. T_A 25°C, f = 1.0 MHz.



sysIO Recommended Operating Conditions

		V _{CCIO}		V _{REF} (V)			
Standard	Min.	Тур.	Max.	Min.	Тур.	Max.	
LVCMOS33 ²	3.135	3.3	3.465	—			
LVCMOS25 ²	2.375	2.5	2.625	—			
LVCMOS18	1.71	1.8	1.89	—	—	—	
LVCMOS15	1.425	1.5	1.575	—			
LVCMOS12 ²	1.14	1.2	1.26	—			
LVTTL33 ²	3.135	3.3	3.465	—	—	—	
PCI33	3.135	3.3	3.465	—		—	
SSTL18_I ² , SSTL18_II ²	1.71	1.8	1.89	0.833	0.9	0.969	
SSTL25_I ² , SSTL25_II ²	2.375	2.5	2.625	1.15	1.25	1.35	
SSTL33_I ² , SSTL33_II ²	3.135	3.3	3.465	1.3	1.5	1.7	
HSTL15_l ²	1.425	1.5	1.575	0.68	0.75	0.9	
HSTL18_I ² , HSTL18_II ²	1.71	1.8	1.89	0.816	0.9	1.08	
LVDS25 ²	2.375	2.5	2.625	—			
MLVDS251	2.375	2.5	2.625	—			
LVPECL33 ^{1, 2}	3.135	3.3	3.465	—			
BLVDS25 ^{1, 2}	2.375	2.5	2.625	—			
RSDS ^{1, 2}	2.375	2.5	2.625	—			
SSTL18D_I ² , SSTL18D_II ²	1.71	1.8	1.89	—	—	—	
SSTL25D_ I ² , SSTL25D_II ²	2.375	2.5	2.625	—	—	—	
SSTL33D_ I ² , SSTL33D_ II ²	3.135	3.3	3.465	—	—	—	
HSTL15D_ I ²	1.425	1.5	1.575	—	—	—	
HSTL18D_ I ² , HSTL18D_ II ²	1.71	1.8	1.89	_	—	—	

Over Recommended Operating Conditions

1. Inputs on chip. Outputs are implemented with the addition of external resistors. 2. Input on this standard does not depend on the value of V_{CCIO} .



sysIO Differential Electrical Characteristics LVDS

Parameter	Description	Test Conditions	Min.	Тур.	Max.	Units
V _{INP} , V _{INM}	Input Voltage		0	_	2.4	V
V _{CM}	Input Common Mode Voltage	Half the Sum of the Two Inputs	0.05	_	2.35	V
V _{THD}	Differential Input Threshold	Difference Between the Two Inputs	+/-100	_	—	mV
I _{IN}	Input Current	Power On or Power Off			+/-10	μA
V _{OH}	Output High Voltage for V_{OP} or V_{OM}	R _T = 100 Ohm	_	1.38	1.60	V
V _{OL}	Output Low Voltage for V_{OP} or V_{OM}	R _T = 100 Ohm	0.9V	1.03	—	V
V _{OD}	Output Voltage Differential	(V _{OP} - V _{OM}), R _T = 100 Ohm	250	350	450	mV
ΔV _{OD}	Change in V _{OD} Between High and Low		_	_	50	mV
V _{OS}	Output Voltage Offset	(V _{OP} + V _{OM})/2, R _T = 100 Ohm	1.125	1.20	1.375	V
ΔV_{OS}	Change in V _{OS} Between H and L			_	50	mV
I _{SA}	Output Short Circuit Current	V _{OD} = 0V Driver Outputs Shorted to Ground	_	_	24	mA
I _{SAB}	Output Short Circuit Current	V _{OD} = 0V Driver Outputs Shorted to Each Other	_	_	12	mA

Over Recommended Operating Conditions

Differential HSTL and SSTL

Differential HSTL and SSTL outputs are implemented as a pair of complementary single-ended outputs. All allowable single-ended output classes (class I and class II) are supported in this mode.

For further information on LVPECL, RSDS, MLVDS, BLVDS and other differential interfaces please see details in additional technical notes listed at the end of this data sheet.

LVDS25E

The top and bottom sides of LatticeXP2 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.







Register-to-Register Performance (Continued)

Function	-7 Timing	Units
DSP IP Functions		
16-Tap Fully-Parallel FIR Filter	198	MHz
1024-pt FFT	221	MHz
8X8 Matrix Multiplication	196	MHz

1. These timing numbers were generated using the ispLEVER design tool. Exact performance may vary with device, design and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.



LatticeXP2 External Switching Characteristics (Continued)

			-7		-6		-5		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
		XP2-5	0.00	—	0.00		0.00		ns
		XP2-8	0.00	—	0.00		0.00		ns
t _{H_DELPLL}	Register with Input Data Delay	XP2-17	0.00	—	0.00		0.00		ns
		XP2-30	0.00	—	0.00	_	0.00	_	ns
		XP2-40	0.00	—	0.00	_	0.00	_	ns
DDR ² and DDF	2 ³ I/O Pin Parameters								
t _{DVADQ}	Data Valid After DQS (DDR Read)	XP2	—	0.29	—	0.29	—	0.29	UI
t _{DVEDQ}	Data Hold After DQS (DDR Read)	XP2	0.71	—	0.71	_	0.71	_	UI
t _{DQVBS}	Data Valid Before DQS	XP2	0.25	—	0.25		0.25		UI
t _{DQVAS}	Data Valid After DQS	XP2	0.25	—	0.25		0.25		UI
f _{MAX_DDR}	DDR Clock Frequency	XP2	95	200	95	166	95	133	MHz
f _{MAX_DDR2}	DDR Clock Frequency	XP2	133	200	133	200	133	166	MHz
Primary Clock									
f _{MAX_PRI}	Frequency for Primary Clock Tree	XP2	—	420	—	357	—	311	MHz
t _{W_PRI}	Clock Pulse Width for Primary Clock	XP2	1	—	1	_	1	_	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Bank	XP2	_	160	_	160	_	160	ps
Edge Clock (ECLK1 and ECLK2)									
f _{MAX_ECLK}	Frequency for Edge Clock	XP2	_	420		357		311	MHz
tw_eclk	Clock Pulse Width for Edge Clock	XP2	1	_	1	_	1	_	ns
tskew_eclk	Edge Clock Skew Within an Edge of the Device	XP2	—	130	—	130	—	130	ps

Over Recommended Operating Conditions

1. General timing numbers based on LVCMOS 2.5, 12mA, 0pf load.

2. DDR timing numbers based on SSTL25.

3. DDR2 timing numbers based on SSTL18.







Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.



Switching Test Conditions

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

 Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	R ₂	CL	Timing Ref.	V _T
	$\infty \qquad \infty \qquad 0 \text{pF} \qquad \frac{\text{LVCMOS } 3.3 = 1.5 \text{V}}{\text{LVCMOS } 2.5 = \text{V}_{\text{CCIO}}/2}$			LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
LVTTL and other LVCMOS settings (L -> H, H -> L)		LVCMOS 1.8 = V _{CCIO} /2			
				LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V _{CCIO} /2	_
LVCMOS 2.5 I/O (Z -> H)	8	1MΩ		V _{CCIO} /2	
LVCMOS 2.5 I/O (Z -> L)	1MΩ	∞		V _{CCIO} /2	V _{CCIO}
LVCMOS 2.5 I/O (H -> Z)	8	100		V _{OH} - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	∞		V _{OL} + 0.10	V _{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.



PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges	of the Device	
D[Edgo] [n 4]	А	DQ
r[Euge] [11-4]	В	DQ
D[Edga] [n 2]	А	DQ
r[Euge] [II-3]	В	DQ
D[Edgo] [n 2]	А	DQ
	В	DQ
P[Edge] [n-1]	А	DQ
	В	DQ
P[Edge] [n]	А	[Edge]DQSn
	В	DQ
P[Edge] [n+1]	А	DQ
	В	DQ
P[Edge] [n+2]	А	DQ
	В	DQ
P[Edge] [n+3]	А	DQ
	В	DQ
For Top and Bottom Edge	es of the Device	
P[Edge] [n-4]	А	DQ
	В	DQ
P[Edge] [n-3]	A	DQ
	В	DQ
P[Edge] [n-2]	A	DQ
. [=090] [=]	В	DQ
P[Edge] [n-1]	A	DQ
. [=090][]	В	DQ
P[Edge] [n]	A	[Edge]DQSn
. [====================================	В	DQ
P[Edge] [n+1]	A	DQ
. [=a90][]	В	DQ
P[Edge] [n+2]	A	DQ
. [=380][=]	В	DQ
P[Edge] [n+3]	A	DQ
. [=390] [0]	В	DQ
P[Edge] [n+4]	A	DQ
. [=390][]	В	DQ

Notes:

1. "n" is a row PIC number.

^{2.} The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the "Signal Names" column of the Signal Descriptions table.



Lead-Free Packaging

Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	5
LFXP2-5E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	5
LFXP2-5E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	5
LFXP2-5E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	5
LFXP2-5E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	5
LFXP2-5E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	5
LFXP2-5E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	5
LFXP2-5E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	5
LFXP2-5E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	5
LFXP2-5E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	5
LFXP2-5E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	5
LFXP2-5E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	8
LFXP2-8E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	8
LFXP2-8E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	8
LFXP2-8E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	8
LFXP2-8E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	8
LFXP2-8E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	8
LFXP2-8E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	8
LFXP2-8E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	8
LFXP2-8E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	8
LFXP2-8E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	8
LFXP2-8E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	8
LFXP2-8E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	17
LFXP2-17E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	17
LFXP2-17E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	17
LFXP2-17E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	17
LFXP2-17E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	17
LFXP2-17E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	17
LFXP2-17E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	17
LFXP2-17E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	17
LFXP2-17E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	17



LatticeXP2 Family Data Sheet Revision History

September 2014

Data Sheet DS1009

Revision History

Date	Version	Section	Change Summary
May 2007	01.1	_	Initial release.
September 2007	01.2	DC and Switching Characteristics	Added JTAG Port Timing Waveforms diagram.
			Updated sysCLOCK PLL Timing table.
		Pinout Information	Added Thermal Management text section.
February 2008	01.3	Architecture	Added LVCMOS33D to Supported Output Standards table.
			Clarified: "This Flash can be programmed through either the JTAG or Slave SPI ports of the device. The SRAM configuration space can also be infinitely reconfigured through the JTAG and Master SPI ports."
			Added External Slave SPI Port to Serial TAG Memory section. Updated Serial TAG Memory diagram.
		DC and Switching Characteristics	Updated Flash Programming Specifications table.
			Added "8W" specification to Hot Socketing Specifications table.
			Updated Timing Tables
			Clarifications for IIH in DC Electrical Characteristics table.
			Added LVCMOS33D section
			Updated DOA and DOA (Regs) to EBR Timing diagrams.
			Removed Master Clock Frequency and Duty Cycle sections from the LatticeXP2 sysCONFIG Port Timing Specifications table. These are listed on the On-chip Oscillator and Configuration Master Clock Characteristics table.
			Changed CSSPIN to CSSPISN in description of $t_{SCS}, t_{SCSS},$ and t_{SCSH} parameters. Removed t_{SOE} parameter.
			Clarified On-chip Oscillator documentation
			Added Switching Test Conditions
		Pinout Information	Added "True LVDS Pairs Bonding Out per Bank," "DDR Banks Bonding Out per I/O Bank," and "PCI capable I/Os Bonding Out per Bank" to Pin Information Summary in place of previous blank table "PCI and DDR Capabilities of the Device-Package Combinations"
			Removed pinout listing. This information is available on the LatticeXP2 product web pages
		Ordering Information	Added XP2-17 "8W" and all other family OPNs.
April 2008	01.4	DC and Switching	Updated Absolute Maximum Ratings footnotes.
		Characteristics	Updated Recommended Operating Conditions Table footnotes.
			Updated Supply Current (Standby) Table
			Updated Initialization Supply Current Table
			Updated Programming and Erase Flash Supply Current Table
			Updated Register to Register Performance Table
			Updated LatticeXP2 External Switching Characteristics Table
			Updated LatticeXP2 Internal Switching Characteristics Table
			Updated sysCLOCK PLL Timing Table

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